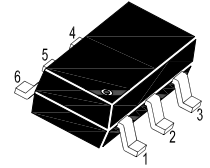
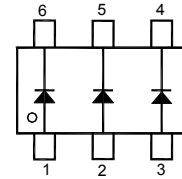


■ Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- Ultra-small surface mount package
- For general purpose switching applications
- High conductance



1. Anode 2. Anode 3. Anode
4. Cathode 5. Cathode 6. Cathode

■ Simplified outline(SOT-363)

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	100	V
Reverse Voltage	V _R	75	V
Average Rectified Forward Current	I _{F(AV)}	200	mA
Forward Continuous Current	I _{FM}	300	mA
Non-Repetitive Peak Forward Current	I _{FSM}	2 1	A
		t = 1 μs t = 1 s	
Power Dissipation	P _{tot}	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{stg}	- 65 to + 150	°C

Characteristics at T_a = 25°C

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I _R = 100 μA	V _{(BR)R}	75	-	V
Forward Voltage at I _F = 1 mA at I _F = 10 mA at I _F = 50 mA at I _F = 150 mA	V _F	- - - -	0.715 0.855 1 1.25	V
Peak Reverse Current at V _R = 20 V at V _R = 75 V at V _R = 25 V, T _J = 150°C at V _R = 75 V, T _J = 150°C	I _R	- - - -	25 1 30 50	nA μA μA μA
Total Capacitance at V _R = 0 V, f = 1 MHz	C _T	-	2	pF
Reverse Recovery Time at I _F = I _R = 10 mA, I _{rr} = 0.1 X I _R , R _L = 100 Ω	t _{rr}	-	4	ns

Power Dissipation vs Ambient Temperature

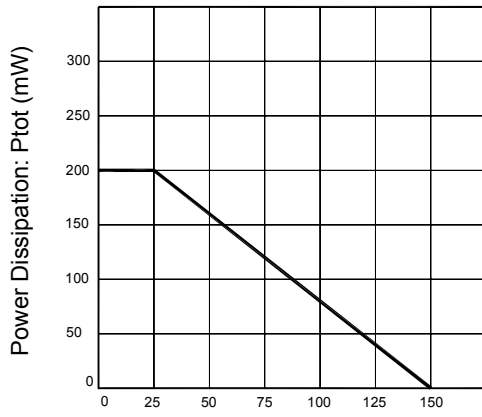


Fig.1 Ambient Temperature: Ta (C)

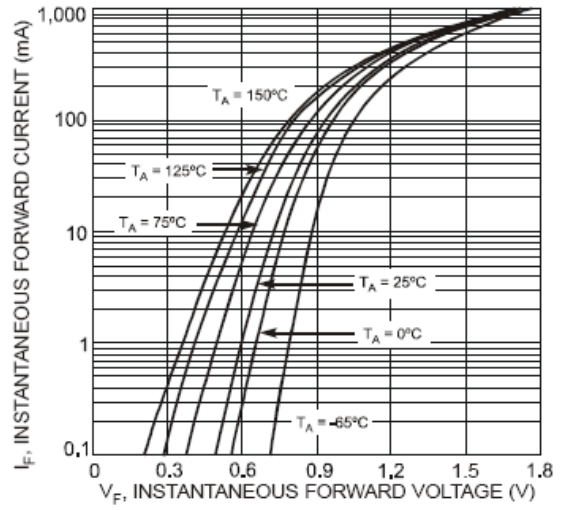


Fig. 2 Typical Forward Characteristics

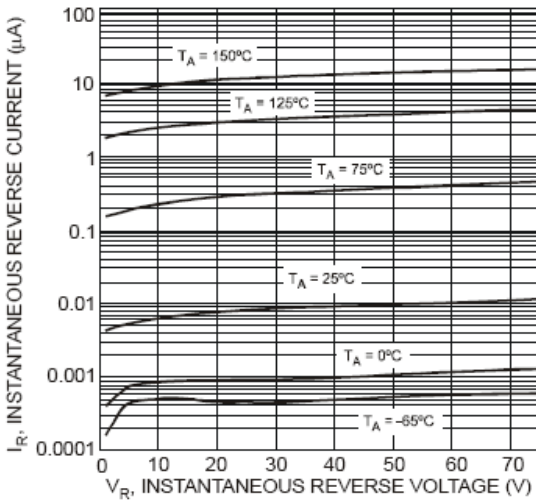


Fig. 3 Typical Reverse Characteristics

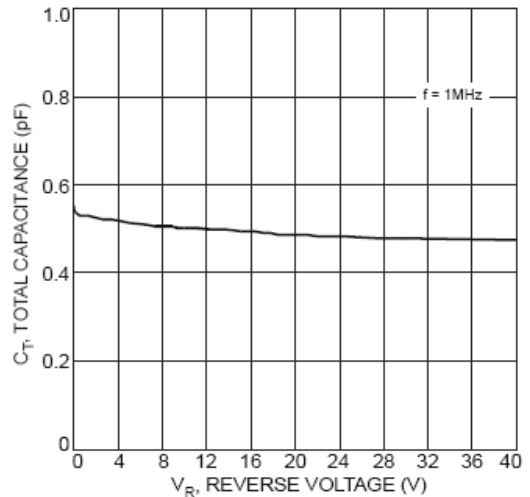
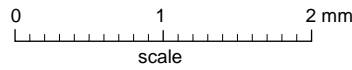
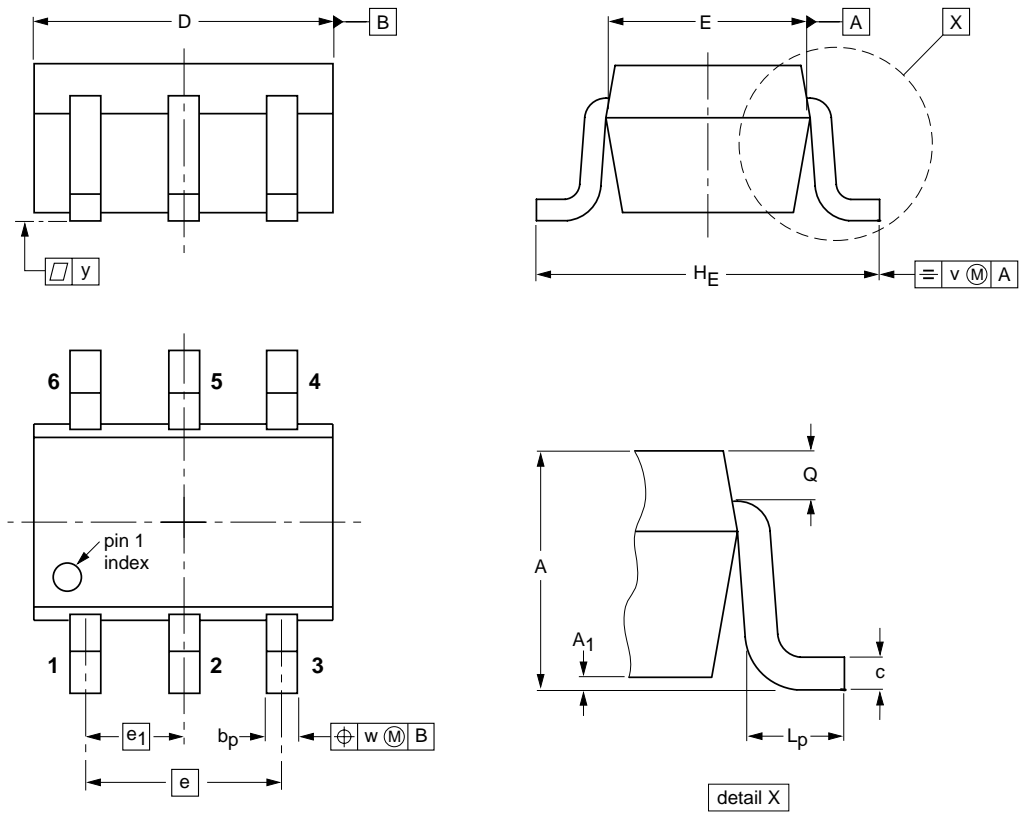


Fig. 4 Typical Total Capacitance

Package Outline

SOT-363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
SOT-363	Tape/Reel, 7" reel	3000	EIA-481-1